Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A magneto-resistance effect element bar exposure method comprising the steps of:

detecting the positions of a plurality of alignment marks formed on a substrate;

correcting an exposure position correction region on the basis of the positions of the detected alignment marks; and

exposing a resist that is coated on the substrate,

wherein a magneto-resistance effect element bar region comprises a plurality of magneto-resistance effect elements arranged in the longitudinal direction of the bar region; and

~~one~~a single exposure position correction region is established for one magneto-resistance effect element bar region.

2. (Original) The magneto-resistance effect element bar exposure method according to claim 1,

wherein one magneto-resistance effect element bar region does not straddle the boundary of the exposure position correction region.

3. (Original) The magneto-resistance effect element bar exposure method according to claim 1,

wherein the exposure is electron beam exposure.

4. (Original) A magneto-resistance effect element bar formation method, comprising the steps of:

developing a resist exposed by means of the magneto-resistance effect element bar exposure method according to claim 1;

forming a magneto-resistance effect element pattern by using a mask constituted by the developed resist;

cutting the magneto-resistance effect element bar from the substrate; and

polishing the cut faces parallel to the longitudinal direction of the magneto-resistance effect element bar.

5-6. (Canceled)

7. (New) The magneto-resistance effect element bar exposure method according to claim 1, wherein a distance between neighboring magneto-resistance effect elements in a thickness direction of the magneto-resistance effect element bar and in a direction perpendicular to the longitudinal direction thereof is equal to or less than 0.05 μm.